

ABSTRACT OF THE DISCLOSURE

5 A method for making a semiconductor device having a
pattern of highly doped regions (6, 6') located some distance
apart in a semiconductor substrate (1) and regions (7, 7',
7'') of low doping located between the highly doped regions
(6, 6'). A diffusion barrier material (5, 5', 5'') is applied
to the semiconductor substrate at the location of the regions
10 of low doping by imprinting with the barrier material in the
pattern of the regions of low doping. The doping material is
applied after or before imprinting with barrier material so
that the highly doped regions are formed essentially between
the barrier material in the substrate. The doping
15 concentrations in the regions of low doping in the highly
doped regions can be freely adjusted independently of one
another so that a relatively low surface resistance can be
obtained for the highly doped regions to give good conducting
contact with the metalisation and a high surface resistance
20 can be achieved in the regions of low doping.